



FUKUCOM COMPANY LTD.

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FLAT P, 3/F., EVEREST INDUSTRIAL CENTRE, 396 KWUN TONG ROAD,
KWUN TONG, KOWLOON, HONG KONG.

TEL: 852-2790 0314 FAX: 852-2790 0206

BAS316WS

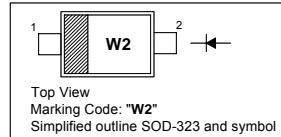
Silicon Epitaxial Planar Switching Diode

Applications

- High-speed switching

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode

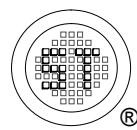


Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}	100	V
Reverse Voltage	V_R	100	V
Continuous Forward Current	I_F	250	mA
Repetitive Peak Forward Current	I_{FRM}	500	mA
Non-Repetitive Peak Forward Current $t = 1 \mu\text{s}$ $t = 1 \text{ ms}$ $t = 1 \text{ s}$	I_{FSM}	4 1 0.5	A
Total Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 1 \text{ mA}$ at $I_F = 10 \text{ mA}$ at $I_F = 50 \text{ mA}$ at $I_F = 150 \text{ mA}$	V_F	0.715 0.855 1 1.25	V
Reverse Current at $V_R = 25 \text{ V}$ at $V_R = 75 \text{ V}$ at $V_R = 25 \text{ V}, T_j = 150^\circ\text{C}$ at $V_R = 75 \text{ V}, T_j = 150^\circ\text{C}$	I_R	30 1 30 50	nA μA μA μA
Diode Capacitance at $V_R = 0 \text{ V}, f = 1 \text{ MHz}$	C_{tot}	1.5	pF
Reverse Recovery Time at $I_F = I_R = 10 \text{ mA}, I_{rr} = 0.1 \times I_R, R_L = 100 \Omega$	t_{rr}	4	ns



Dated : 15/06/2009



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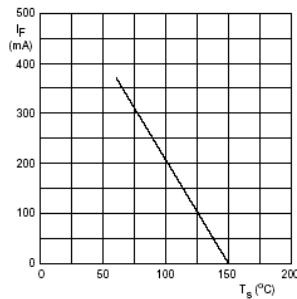


Fig. 1 Maximum permissible continuous forward current as a function of soldering point temperature.

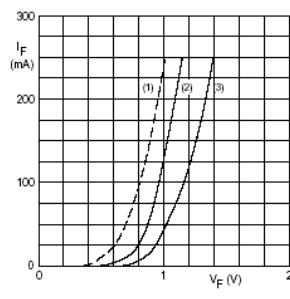
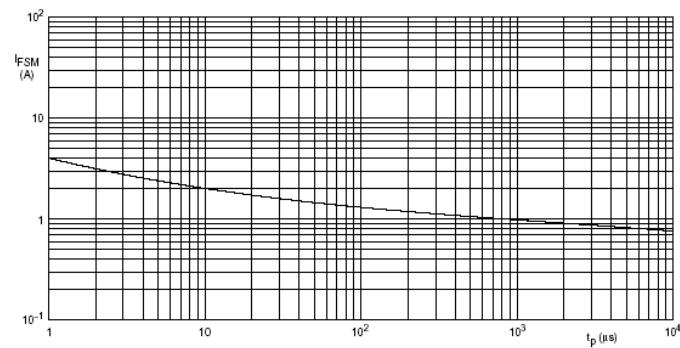


Fig. 2 Forward current as a function of forward voltage.



Based on square wave currents.
T_j = 25 °C prior to surge.

Fig. 3 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

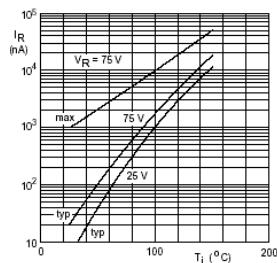


Fig. 4 Reverse current as a function of junction temperature.

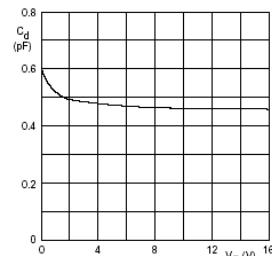
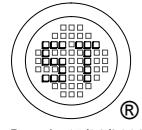


Fig. 5 Diode capacitance as a function of reverse voltage; typical values.



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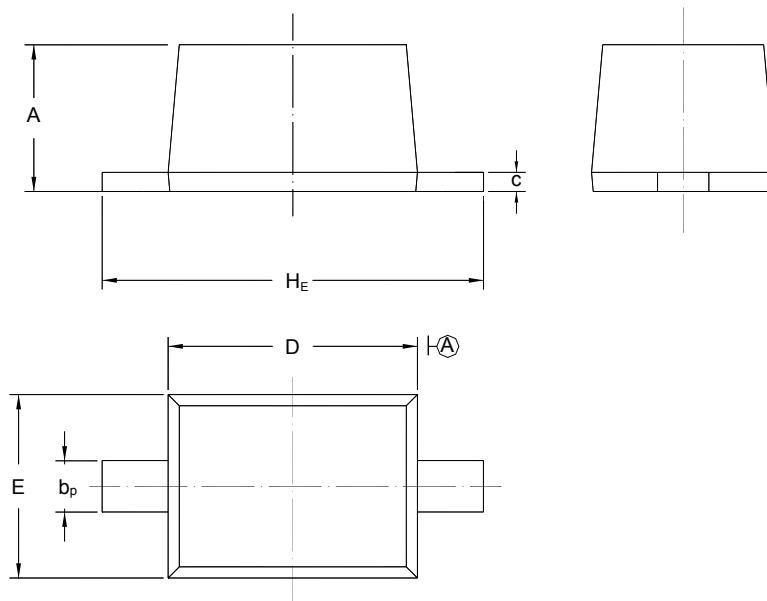
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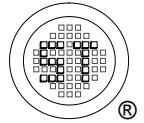
PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



UNIT	A	b _p	C	D	E	H _E
mm	1.10 0.80	0.40 0.25	0.15 0.00	1.80 1.60	1.35 1.15	2.80 2.30



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